



ZVP2106G

60V P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = +25°C	
-60V	5Ω @ V _{GS} = -10V	-450mA	

Description

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- DC-DC Converters

Features and Benefits

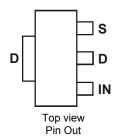
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS compliant (Note 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.112 grams (approximate)



Top View



Ordering Information (Note 4)

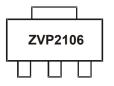
Product	Case	Quantity per reel
ZVP2106GTA	SOT223	1,000

SOT223

Note:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZVP2106 = Product type Marking Code



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DS}	-60	V
Gate Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I _D	-450	M A
Pulsed Drain Current	I _{DM}	-4	A

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Power Dissipation	P _{TOT}	2	W
Storage Temperature Range	T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

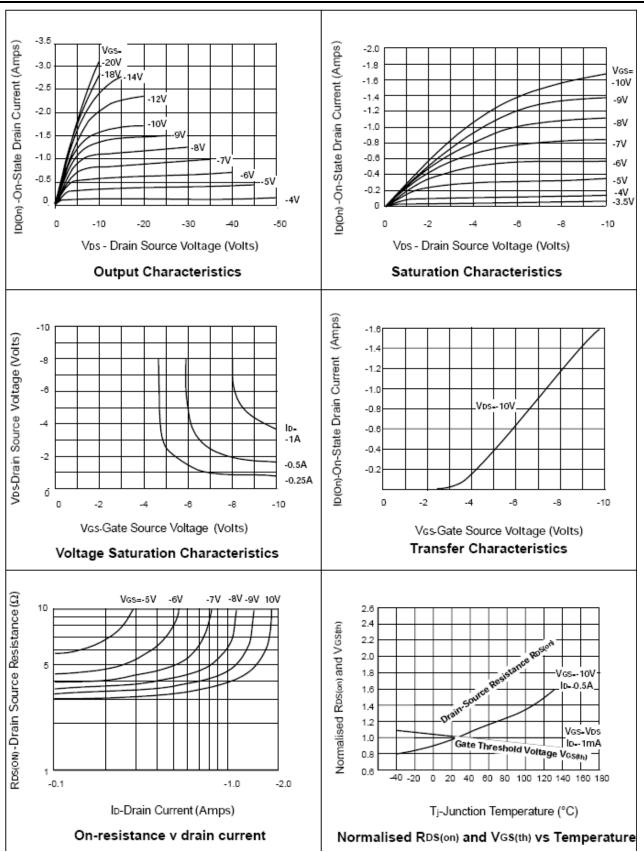
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Static Characteristics	•		•		•	
Drain-Source Breakdown Voltage	BV _{DSS}	-60	_	_	V	I _D = -1mA, V _{GS} = 0V
Gate-Source Threshold Voltage	V _{GS(th)}	-1.5	_	-3.5	V	I _D = -1mA, V _{DS} = V _{GS}
Gate-Body Leakage	I _{GSS}	_	_	20	nA	V _{GS} = ±20V, V _{DS} = 0V
		_	_	-0.5	μΑ	V _{DS} = -60V, V _{GS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}			-100	μΑ	V _{DS} = -48V, V _{GS} = 0V, T= +125°C (Note 6)
On-State Drain Current (Note 5)	I _{D(on)}	-1	_	_	Α	V _{DS} = -18V, V _{GS} = -10V
Static Drain-Source On-State Resistance (Note 5)	R _{DS(on)}	_	_	5	Ω	$V_{GS} = -10V, I_D = -500mA$
Forward Transconductance (Note 5 & 6)	9 fS	150	_	_	mS	$V_{DS} = -18V, I_D = -500mA$
Dynamic Characteristics (Note 6)						
Input Capacitance	C _{iss}	_	_	100		
Common Source Output Capacitance	Coss	_	_	60	pF	V _{DS} = -18V, V _{GS} = 0V, f=1MHz
Reverse Transfer Capacitance	Crss	_	_	20		
Turn-On Delay Time (Note 7)	t _{d(on)}	_	_	7		
Rise Time (Note 7)	t _r	_	_	5	ns $V_{DD} = -18V, I_D = -500 \text{mA}$	\\ - 40\\ I - 500mA
Turn-Off Delay Time (Note 7)	t _{d(off)}	_	_	12		V _{DD} = -18V, I _D = -500mA
Fall Time (Note 7)	f _f	_	_	15		

Notes:

- 5. Measured under pulsed conditions. Width=300 μ s. Duty cycle \leq 2%.
- 6. Sample test. 7. Switching times measured with 50Ω source impedance and <5ns rise time on a pulse generator.

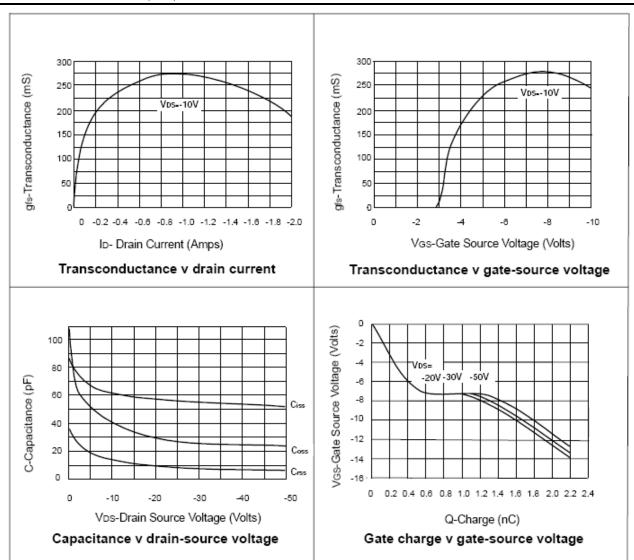


Typical Characteristics





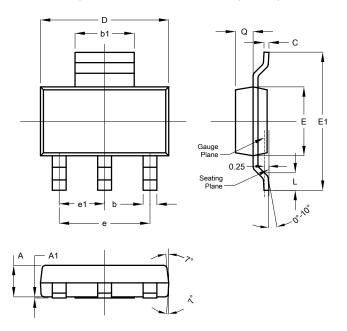
Typical Characteristics (cont.)





Package Outline Dimensions

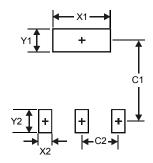
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b	0.60	0.80	0.70	
b1	2.90	3.10	3.00	
C	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
e	-	ı	4.60	
e1	-	-	2.30	
L	0.85	1.05	0.95	
Q	0.84	0.94	0.89	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
X1	3.3
X2	1.2
Y1	1.6
Y2	1.6
C1	6.4
C2	2.3



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